

REMARKS

Claims 1-3, 5, 9-11, and 21 are pending in this application. Claim 3 was cancelled. Claims 1 and 5 were amended and new claims 23-29 were added to more distinctly claim the invention. Support for the new and amended claims can be found in the specification. No new matter has been added.

Attached is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "VERSION WITH MARKINGS TO SHOW CHANGES MADE."

The Examiner objected to certain references in the information disclosure statement. A copy of the Japanese Patent 75229 and U.S. Application Serial Number 09/268,203 were not included. To overcome such objections, Applicants submit U.S. Patent No. 5,089,441 that is related to the Japanese patent as evidenced by the attached search results for Dialog. Applicants also include a copy of U.S. Serial Number. 09/268,203, commonly assigned.

Claim 1 is objected to. The term "undesirable influence" does not include a positive limitation. Accordingly, Applicants have provided such limitation in claim 1, as shown above, as discussed with the Examiner. Applicants have also changed the "containing" language in claim 1. Accordingly, claim 1 should be free from any objections.

Claims 1-3, 5, 9-11, and 21 were rejected under 35 U.S.C. §112, first paragraph. Applicants have discussed such rejection with Examiner Ahmed. Claim 1 has been amended to eliminate the recitation of "atoms," which should render the rejection moot. The Examiner also rejected claims 1-3, 5, 9-11, and 21 under 35 U.S.C. §112, second paragraph. Accordingly, claim 1 has been amended, which should render the objection moot.

New claims 23 through 29 were added. No new matter has been introduced thereby. Applicants respectfully request for such claims to be added for

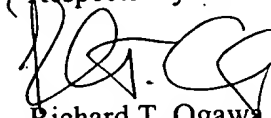
SHUZO FUJIMURA et al.
Application No.: 09/328,939
Page 5

examination and allowance. Such claims were derived from claims 1-3, 9, 9-11, and 21, which have been pending.

CONCLUSION

In view of the foregoing, Applicants believe all claims now pending in this Application are in condition for allowance and an action to that end is urged. If the Examiner believes a telephone conference would aid in the prosecution of this case in any way, please call the undersigned at 650-326-2400.

Respectfully submitted,



Richard T. Ogawa
Reg. No. 37,692

TOWNSEND and TOWNSEND and CREW LLP
Two Embarcadero Center, 8th Floor
San Francisco, California 94111-3834
Tel: (650) 326-2400
Fax: (415) 576-0300
RTO/acc
PA 3246730 v1

VERSION WITH MARKINGS TO SHOW CHANGES MADE

1. (Amended) A method of surface treatment in a substantially downstream position of a plasma source to substantially **[prevent]** be free from an undesirable influence of a reactive species from the plasma source, where an object to be processed is downstream from the plasma source, the method comprising generating a plasma discharge including a gas-C, the gas-C comprising a Gas-A molecule **[containing]** including essentially hydrogen as an element and a Gas-B **[containing]** including essentially a **[halogen and/or]** a halide; wherein said plasma discharge is substantially free from an oxygen bearing species; and wherein the Gas B is selected from **[chlorine,]** hydrogen chloride[, **bromine,**] or hydrogen bromide; wherein Gas C comprises a flow rate defined as a ratio of an amount of hydrogen **[atom]** in Gas-B to that in Gas-A is larger than 1/480.

2. The method of claim 1 further comprising injecting a Gas-D in the downstream of the plasma of Gas-C to treat the object comprising a surface in a downstream position of the Gas-D injection.

3. (Canceled)

5. (Amended) The method of claim 1 [3], wherein Gas-B does not contain an oxygen atom.

9. The method of claim 2, wherein gas containing silicon as its element is used as Gas-D.

10. The method of claim 2, wherein gas containing carbon as its element is used as Gas-D.

11. The method of claim 2, wherein gas containing fluorine as its element is used as Gas-D.

21. The method of claim 1 wherein the method is provided to substantially prevent physical damage caused by a high energy particle.

23. (New) A method of surface treatment in a substantially downstream position of a plasma source, where an object to be processed is downstream from the plasma source, the method comprising generating a plasma discharge including a gas-C, the gas-C comprising a Gas-A molecule including essentially hydrogen as an element and a Gas-B including essentially a halogen and a hydrogen bearing species; wherein said plasma discharge is substantially free from an oxygen bearing species; and wherein the Gas B is selected from at least a chlorine, bromine, iodine, or fluorine; wherein Gas C comprises a flow rate defined as a ratio of an amount of hydrogen in Gas-B to that in Gas-A is larger than 1/480.

24. (New) The method of claim 23 further comprising injecting a Gas-D in the downstream of the plasma of Gas-C to treat the object comprising a surface in a downstream position of the Gas-D injection.

25. The method of claim 23 wherein Gas-B does not contain an oxygen atom.

26. The method of claim 23 wherein gas containing silicon as its element is used as Gas-D.

27. The method of claim 23 wherein gas containing carbon as its element is used as Gas-D.

28. The method of claim 23 wherein gas containing fluorine as its element is used as Gas-D.

29. The method of claim 23 wherein the method is provided to substantially prevent physical damage caused by a high energy particle.